

SANYO Semiconductors DATA SHEET

2SA1291 / 2SC3255 — FNP / NPN Epitaxial Planar Silicon Transistors 60V / 10A High-Speed Switching Applications

Applications

- · Various inductance lamp drivers for electrical equipment.
- · Inverters, converters (flash, fluorescent lamp lighting circuit).
- · Power amp (high power car stereo, motor controller).
- · High-speed switching (switching regulator, driver).

Features

- · Low saturation voltage.
- · Excellent current dependence of hFE.
- · Short switching time.

Specifications (): 2SA1291

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)80	V
Collector-to-Emitter Voltage	VCEO		(-)60	V
Emitter-to-Base Voltage	VEBO		(-)5	V
Collector Current	IC		(-)10	Α
Collector Current (Pulse)	ICP		(-)12	Α
Collector Dissipation	Do.		1.75	W
	PC	Tc=25°C	40	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ІСВО	V _{CB} =(-)40V, I _E =0A			(-)0.1	mA
Emitter Cutoff Current	IEBO	VEB=(-)4V, IC=0A			(-)0.1	mA
DC Current Gain	hFE	V _{CE} =(-)2V, I _C =(-)1A	70*		280*	

Continued on next page.

^{*:} The 2SA1291/2SC3255 are classified by 1A hFE as follows:

Rank	Rank Q		S		
hFE	70 to 140	100 to 200	140 to 280		

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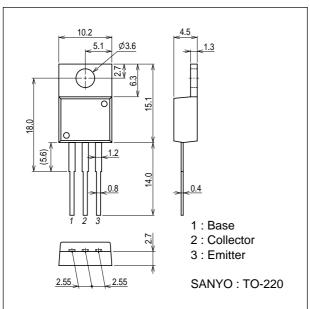
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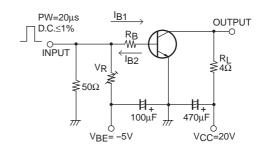
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Gain-Bandwidth Product	fŢ	V _{CE} =(-)5V, I _C =(-)1A		100		MHz
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =(-)5A, I _B =(-)0.25A			(-)0.4	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=(-)1mA, IE=0A	(-)80			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=(-)1mA, RBE=∞	(-)60			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(-)1mA, I _C =0A	(-)5			V
Turn-On Time	ton	See specified Test Circuit.		0.1		μs
Storage Time	t _{stg}	See specified Test Circuit.		0.5		μs
Fall Time	t _f	See specified Test Circuit.		0.1		μs

Package Dimensions

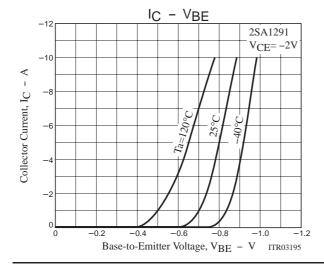
unit : mm (typ) 7507-001

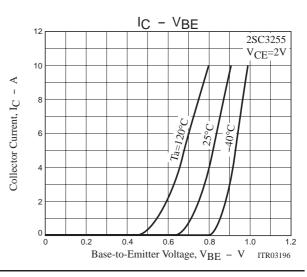


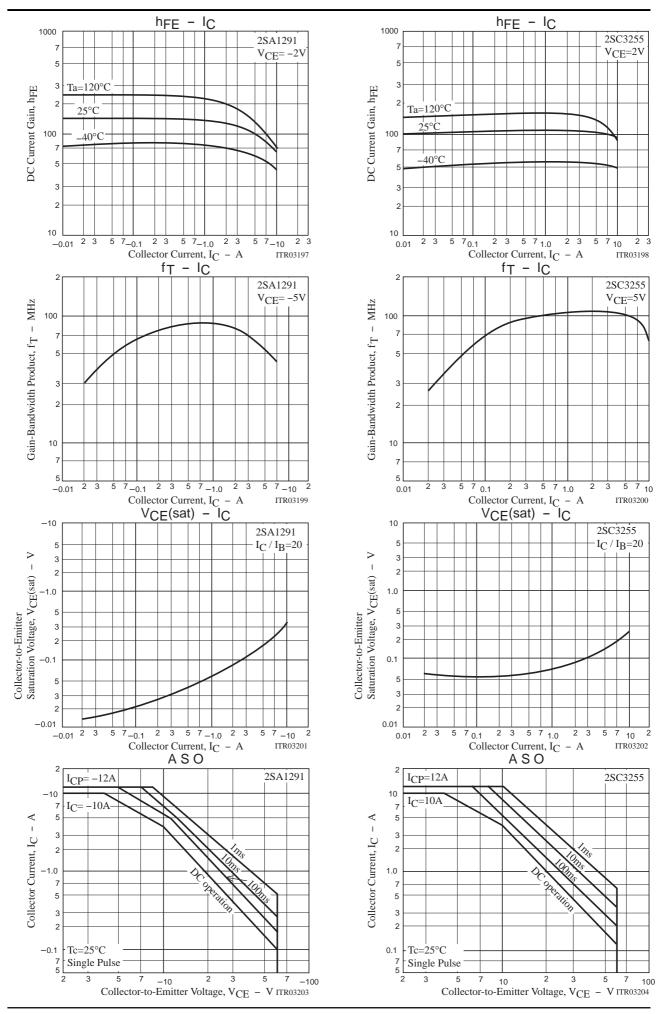
Switching Time Test Circuit



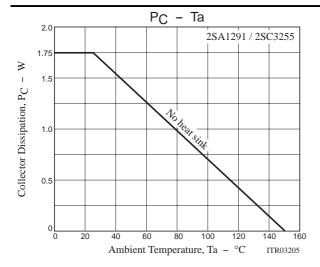
 $20I_{B1} = -20I_{B2} = I_C = 5A$ For PNP, the polarity is reversed.

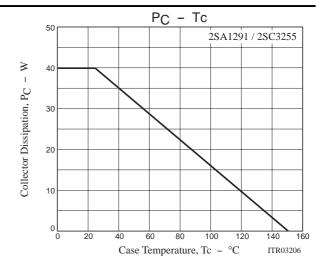






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